

## High-Speed $\pm 100\text{V}$ 2.5A Two-or-Three-Level Ultrasound Pulsers

### Features

- HVCMOS<sup>®</sup> Technology for High Performance
- High Density Integration AC-coupled Pulser
- 0V to  $\pm 100\text{V}$  Output Voltage
- $\pm 2.5\text{A}$  Source and Sink Minimum Pulse Current
- Up to 35 MHz Operating Frequency
- 2 ns Matched Delay Times
- 2.5V, 3.3V or 5V CMOS Logic Interface
- Built-in Two-terminal Low-noise Interface for HV7361
- Low Power Consumption and No Floating Power Supply Rails or Decoupling Capacitors

### Applications

- Medical Ultrasound Imaging
- Piezoelectric Transducer Drivers
- Ultrasound Industrial NDT
- Pulse Waveform Generator

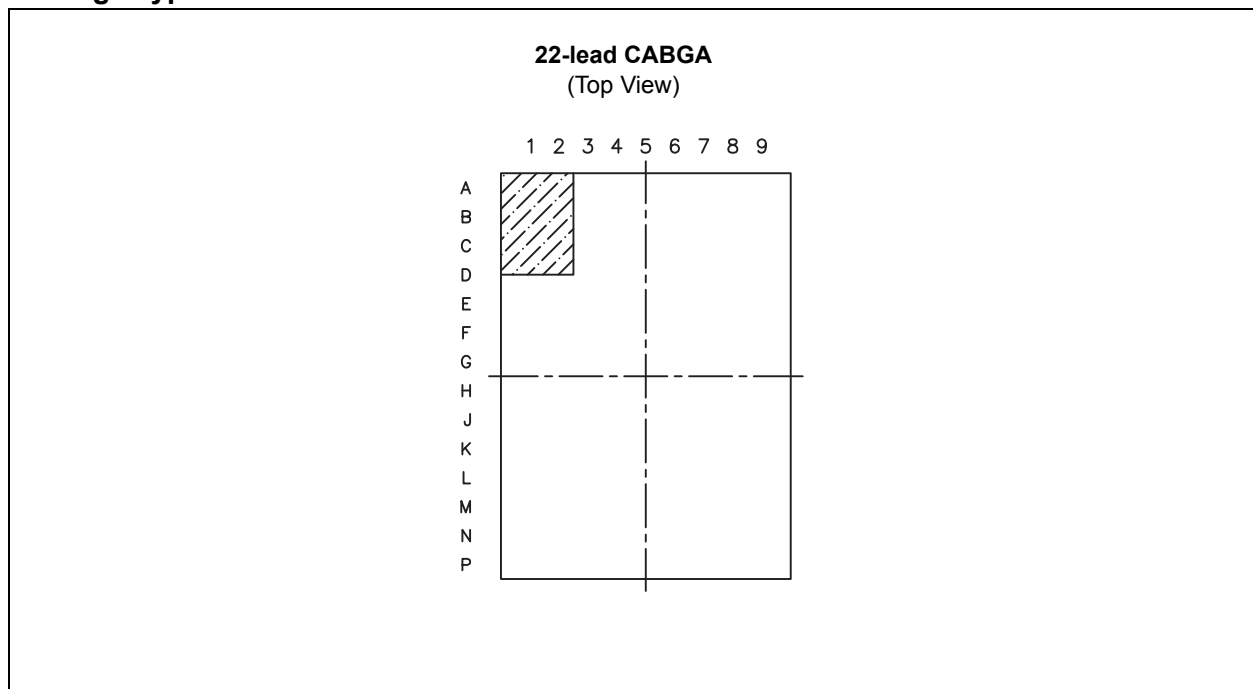
### General Description

HV7360/HV7361 are high-voltage and high-speed pulse generators with built-in fast return-to-zero damping Field-Effect Transistors (FETs). An added feature to HV7361 is an integrated two-terminal low-noise T/R switch. These integrated circuits are designed not only for portable medical ultrasound image devices but also for NDT and test equipment applications.

Both HV7360/HV7361 are composed of controller logic interface circuits, level translators and AC-coupled Metal Oxide Semiconductor Field-Effect Transistor (MOSFET) gate drivers. They also have high-voltage and high-current P-channel and N-channel MOSFETs as output stages.

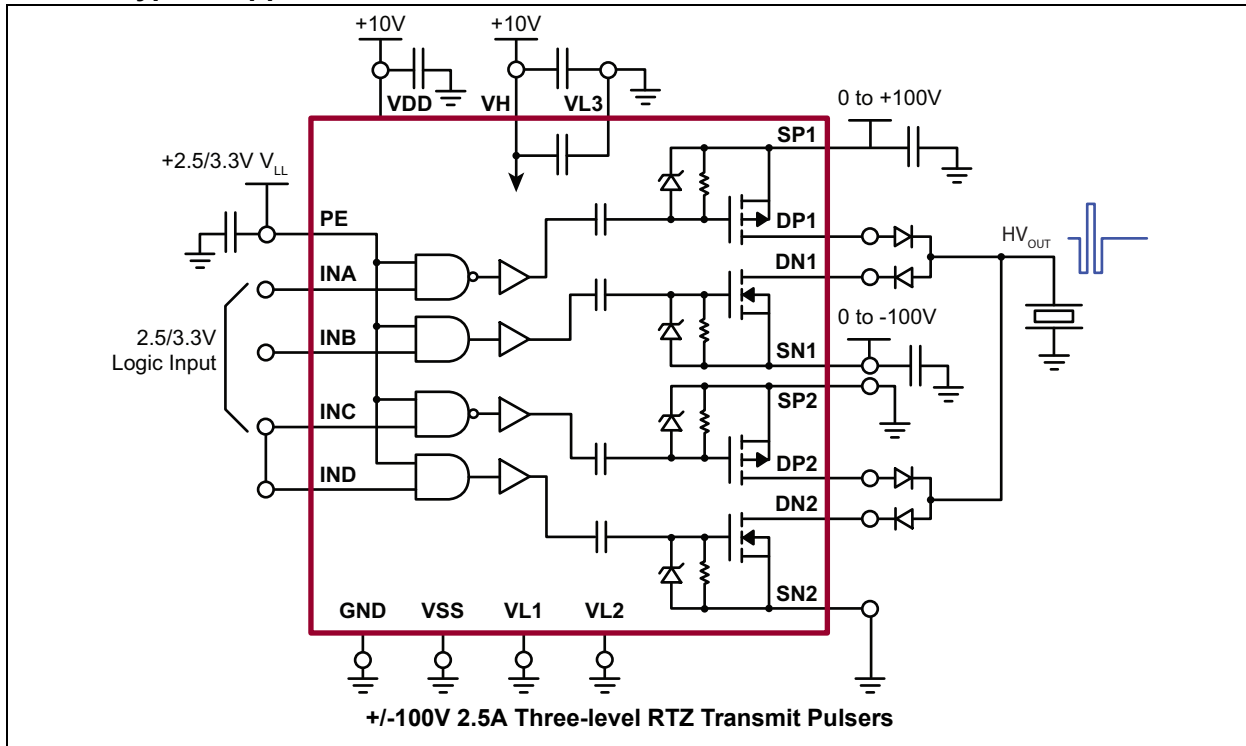
The peak output currents of each channel are guaranteed to be over  $\pm 2.5\text{A}$  with up to  $\pm 100\text{V}$  of pulse swing. The AC coupling topology for the gate drivers not only saves two floating voltage supplies but also makes the PCB layout easier.

### Package Type

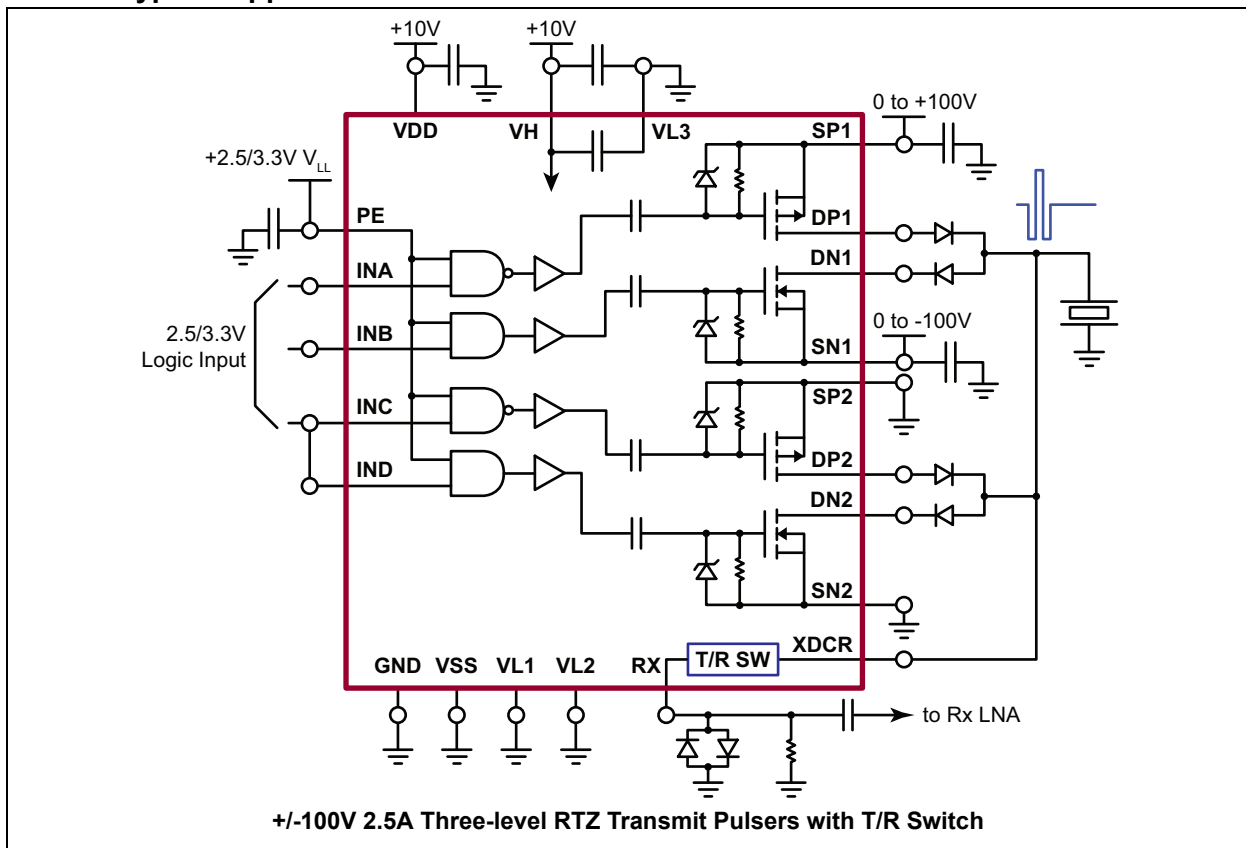


# HV7360/HV7361

## HV7360 Typical Application Circuit



## HV7361 Typical Application Circuit



## 1.0 ELECTRICAL CHARACTERISTICS

### Absolute Maximum Ratings †

Chip Power Supply Voltage ( $V_{DD}-V_{SS}$ ) .....	-0.5 to +12.5V
$V_H$ Output High Supply Voltage .....	$V_L-0.5$ to $V_{DD} +0.5V$
$V_L$ Output Low Supply Voltage.....	$V_{SS}-0.5V$ to $V_H +0.5V$
$V_{SS}$ Low Side Supply Voltage .....	-6 to +0.5V
Differential High Voltage ( $V_{SP1}-V_{SN1}$ ), ( $V_{SP2}-V_{SN2}$ ).....	+220V
$V_{SP1,2}$ Positive High Voltage.....	-0.5 to +110V
$V_{SN1,2}$ Negative High Voltage .....	+0.5 to -110V
All Logic Input Voltages.....	$V_{SS}-0.5V$ to GND +5.5V
Rx to XDCR Differential Drop.....	±140V
Coupling Capacitor Breakdown Voltage.....	±110V
Maximum Junction Temperature.....	125°C
Operating Temperature .....	-20 to +85°C

† **Notice:** Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

### OPERATING SUPPLY VOLTAGES AND CURRENT

**Electrical Specifications:** GND = 0V,  $V_H = V_{DD} = +10V$ ,  $V_L = V_{SS} = 0V$ ,  $V_{PE} = 3.3V$ ,  $V_{PP} = +100V$ ,  $V_{NN} = -100V$ ,  $T_A = 25^\circ C$  unless otherwise specified.

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
Logic Supply Voltage Range	$V_{LL}$	2.25	—	3.63	V	
Supply Voltage	$V_{DD}-V_{SS}$	4.75	—	11.5	V	$4 \leq V_{DD} \leq 11.5V$
Low Side Supply Voltage	$V_{SS}$	-5.5	—	0	V	
Gate Drive High Side Voltage	$V_H$	$V_{SS}+4$	—	$V_{DD}$	V	$V_H-V_L \geq 4V$
Gate Drive Low Side Voltage	$V_L$	$V_{SS}$	—	$V_{DD}-4$	V	
Output Positive High Voltage	$V_{SP1,2}$	0	—	100	V	
Output Negative High Voltage	$V_{SN1,2}$	-100	—	0	V	
$V_{DD}$ Quiescent Current	$I_{DDQ}$	—	50	—	µA	No input transitions, PE = 0
$V_H$ Quiescent Current	$I_{HQ}$	—	2	—	µA	
$V_{DD}$ Quiescent Current	$I_{DDQ}$	—	1	—	mA	No input transitions, PE = 1
$V_H$ Quiescent Current	$I_{HQ}$	—	2	—	µA	
$V_{DD}$ Average Current	$I_{DD}$	—	4	—	mA	One channel On at 5 MHz, No load
$V_H$ Average Current	$I_H$	—	10	—	mA	
Input Logic Voltage High	$V_{IH}$	$V_{PE}-0.3$	—	$V_{PE}$	V	For logic inputs INA, INB, INC and IND
Input Logic Voltage Low	$V_{IL}$	0	—	0.3	V	
Input Logic Current High	$I_{IH}$	—	—	1	µA	
Input Logic Current Low	$I_{IL}$	—	—	1	µA	
PE Input Logic Voltage High	$V_{PEH}$	1.7	3.3	5.25	V	For logic input PE
PE Input Logic Voltage Low	$V_{PEL}$	0	—	0.3	V	
PE Input Impedance to GND	$R_{INPE}$	100	—	—	kΩ	

# HV7360/HV7361

## AC ELECTRICAL CHARACTERISTICS

**Electrical Specifications:** GND = 0V,  $V_H = V_{DD} = +10V$ ,  $V_L = V_{SS} = 0V$ ,  $V_{PE} = 3.3V$ ,  $V_{PP} = +100V$ ,  $V_{NN} = -100V$ ,  $T_A = 25^\circ C$  unless otherwise specified.

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
Input or PE Rise and Fall Time	$t_{irf}$	—	—	10	ns	Logic input edge speed requirement
Input to Output Delay	$t_{d1-4}$	—	7.5	—	ns	$R_{LOAD} = 1\Omega$
Output Rise and Fall Time	$t_{rff1-2}$	—	9.5	—	ns	$C_{LOAD} = 330\text{ pF}$ , $R_{LOAD} = 2.5\text{ k}\Omega$
Rise and Fall Time Matching	$\Delta t_{rf}$	—	2	—	ns	Channel to channel
Propagation Matching	$\Delta t_{dC2C}$	—	1	—		
Propagation Delay Matching	$\Delta t_{dD2D}$	—	$\pm 2$	—	ns	Device to device delay match
PE On-time	$t_{PE-ON}$	—	—	5	$\mu s$	$V_{PE} = 1.7 \sim 5.25V$ , $V_{DD} = 7.5 \sim 11.5V$ , $-20 \sim 85^\circ C$
PE Off-time	$t_{PE-OFF}$	—	—	4		
Output to MOSFET Gate Cap	$C_{OG}$	—	10	—	nF	100V X7S
$V_H$ to $V_{L3}$ Decoupling Cap	$C_{VH}$	—	0.22	—	$\mu F$	16V X7R

## ELECTRICAL CHARACTERISTICS

**Electrical Specifications:** GND = 0V,  $V_H = V_{DD} = +10V$ ,  $V_L = V_{SS} = 0V$ ,  $V_{PE} = 3.3V$ ,  $V_{PP} = +100V$ ,  $V_{NN} = -100V$ ,  $T_A = 25^\circ C$  unless otherwise specified.

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
<b>PULSER AND DAMPING P-CHANNEL MOSFET</b>						
<b>DC PARAMETERS</b>						
Drain-to-source Breakdown Voltage	$BV_{DSS}$	-200	—	—	V	$V_{GS} = 0V$ , $I_D = -2\text{ mA}$
Gate Threshold Voltage	$V_{GS(th)}$	-1	—	-2.4	V	$V_{GS} = V_{DS}$ , $I_D = -1\text{ mA}$
Change in $V_{GS(th)}$ with Temperature	$\Delta V_{GS(th)}$	—	—	4.5	mV/ $^\circ C$	$V_{GS} = V_{DS}$ , $I_D = -1\text{ mA}$
Gate-to-source Shunt Resistor	$R_{GS}$	10	—	50	k $\Omega$	$I_{GS} = 100\text{ }\mu A$ , if applied
Gate-to-source Zener Voltage	$V_{ZGS}$	13.2	—	25	V	$I_{GS} = -2\text{ mA}$ , if applied
Zero-gate Voltage Drain Current	$I_{DSS}$	—	—	-10	$\mu A$	$V_{DS} = \text{Maximum rating}$ , $V_{GS} = 0V$
		—	—	-1	mA	$V_{DS} = 0.8\text{ maximum rating}$ , $V_{GS} = 0V$ , $T_A = 125^\circ C$
ON-state Drain Current	$I_{D(ON)}$	-1.2	—	—	A	$V_{GS} = -5V$ , $V_{DS} = -25V$
		-2.3	-2.5	—		$V_{GS} = -10V$ , $V_{DS} = -50V$
Static Drain-to-source ON-state Resistance	$R_{DS(ON)}$	—	—	8.5	$\Omega$	$V_{GS} = -5V$ , $I_D = -150\text{ mA}$
		—	—	7		$V_{GS} = -10V$ , $I_D = -1A$
Change in $R_{DS(ON)}$ with Temperature	$\Delta R_{DS(ON)}$	—	—	1	%/ $^\circ C$	$V_{GS} = -10V$ , $I_D = -1\text{ mA}$
<b>AC PARAMETERS</b>						
Forward Transconductance	$G_{FS}$	400	—	—	mmho	$V_{DS} = -25V$ , $I_D = -500\text{ mA}$
Input Capacitance	$C_{ISS}$	—	75	—	pF	$V_{GS} = 0V$ , $V_{DS} = -25V$ , $f = 1\text{ MHz}$
Common Source Output Capacitance	$C_{OSS}$	—	21	—		
Reverse Transfer Capacitance	$C_{RSS}$	—	6.5	—		
<b>DIODE PARAMETERS</b>						
Diode Forward Voltage Drop	$V_{SBD}$	—	—	1.8	V	$V_{GS} = 0V$ , $I_{SD} = 500\text{ mA}$
Reverse Recovery Time of Body Diode	$t_{rrBD}$	—	300	—	ns	
<b>PULSER AND DAMPING N-CHANNEL MOSFET</b>						
<b>DC PARAMETERS</b>						
Drain-to-source Breakdown Voltage	$BV_{DSS}$	200	—	—	V	$V_{GS} = 0V$ , $I_D = 2\text{ mA}$
Gate Threshold Voltage	$V_{GS(th)}$	1	—	2.4	V	$V_{GS} = V_{DS}$ , $I_D = 1\text{ mA}$

## ELECTRICAL CHARACTERISTICS (CONTINUED)

**Electrical Specifications:** GND = 0V,  $V_H = V_{DD} = +10V$ ,  $V_L = V_{SS} = 0V$ ,  $V_{PE} = 3.3V$ ,  $V_{PP} = +100V$ ,  $V_{NN} = -100V$ ,  $T_A = 25^\circ C$  unless otherwise specified.

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
Change in $V_{GS(th)}$ with Temperature	$\Delta V_{GS(th)}$	—	—	-4.5	mV/ $^\circ C$	$V_{GS} = V_{DS}$ , $I_D = 1\text{ mA}$
Gate-to-source Shunt Resistor	$R_{GS}$	10	—	50	k $\Omega$	$I_{GS} = 100\ \mu A$
Gate-to-source Zener Voltage	$V_{ZGS}$	13.2	—	25	V	$I_{GS} = 2\text{ mA}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	10	$\mu A$	$V_{DS} = \text{Maximum rating}$ , $V_{GS} = 0V$
		—	—	1	mA	$V_{DS} = 0.8\text{ maximum rating}$ , $V_{GS} = 0V$ , $T_A = 125^\circ C$
ON-state Drain Current	$I_{D(ON)}$	1.3	—	—	A	$V_{GS} = 5V$ , $V_{DS} = 25V$
		2.3	2.5	—		$V_{GS} = 10V$ , $V_{DS} = 50V$
Static Drain-to-source ON-state Resistance	$R_{DS(ON)}$	—	—	6.5	$\Omega$	$V_{GS} = 5V$ , $I_D = 150\text{ mA}$
		—	—	6		$V_{GS} = 10V$ , $I_D = 1A$
Change in $R_{DS(ON)}$ with Temperature	$\Delta R_{DS(ON)}$	—	—	1	%/ $^\circ C$	$V_{GS} = 10V$ , $I_D = 1A$
<b>AC PARAMETERS</b>						
Forward Transconductance	$G_{FS}$	400	—	—	mmho	$V_{DS} = 25V$ , $I_D = 500\text{ mA}$
Input Capacitance	$C_{ISS}$	—	56	—	pF	$V_{GS} = 0V$ , $V_{DS} = 25V$ , $f = 1\text{ MHz}$
Common Source Output Capacitance	$C_{OSS}$	—	13	—		
Reverse Transfer Capacitance	$C_{RSS}$	—	2	—		
<b>DIODE PARAMETERS</b>						
Diode Forward Voltage Drop	$V_{SBD}$	—	—	1.8	V	$V_{GS} = 0V$ , $I_{SD} = 500\text{ mA}$
Reverse Recovery Time of Body Diode	$t_{rrBD}$	—	300	—	ns	

## HV7631 T/R SWITCH CHARACTERISTICS

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
Breakdown Voltage from XDCR to Rx	$B_{VA-B}$	$\pm 130$	—	—	V	$I_{A-B} = \pm 1\text{ mA}$
Switch-on Resistance from XDCR to Rx	$R_{SW}$	—	15	—	$\Omega$	$I_{A-B} = \pm 5\text{ mA}$
$V_{A-B}$ Trip Point to Turn Off	$V_{TRIP}$	—	$\pm 1$	$\pm 2$	V	
Switch Turn-off Voltage	$V_{OFF}$	—	$\pm 2$	—	V	$I_{A-B} = \pm 1\text{ mA}$
Switch-off Current	$I_{A-B(OFF)}$	—	$\pm 200$	$\pm 300$	$\mu A$	$V_{A-B} = \pm 130V$
Peak Switching Current	$I_{PEAK}$	—	$\pm 60$	—	mA	
Turn-off Time	$T_{OFF}$	—	—	20	ns	
Turn-on Time	$T_{ON}$	—	—	20	ns	
Switch-on Capacitance from A to B or B to A	$C_{SW(ON)}$	—	21	—	pF	SW = On
Switch-off Capacitance from A to B or B to A	$C_{SW(OFF)}$	—	15	—	pF	$V_{SW} = 25V$
Small Signal Bandwidth	BW	—	100	—	MHz	$R_{LOAD} = 50\Omega$

# HV7360/HV7361

## TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless otherwise noted, for all specifications $T_A = T_J = +25^\circ\text{C}$ .						
Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
<b>TEMPERATURE RANGES</b>						
Maximum Junction Temperature	$T_{J(\text{MAX})}$	—	125	—	$^\circ\text{C}$	
Operating Temperature	$T_A$	-20	—	+85	$^\circ\text{C}$	
<b>PACKAGE THERMAL RESISTANCE</b>						
22-Lead CABGA	$\theta_{JA}$	—	106	—	$^\circ\text{C/W}$	

## POWER-UP AND POWER-DOWN SEQUENCE (Note 1)

Power-Up		Power-Down	
Step	Description	Step	Description
1	$V_{LL}$	1	PE inactive
2	$V_{DD}$ , $V_H$ , $V_{SS}$ and $V_L$ with signal logic low	2	$V_{PP}$ and $V_{NN}$ off
3	$V_{PP}$ and $V_{NN}$	3	$V_{DD}$ , $V_H$ , $V_{SS}$ and $V_L$ off
4	PE active	4	$V_{LL}$ off

**Note 1:** Powering up or down in any arbitrary sequence will not cause any damage to the device. The power-up sequence and power-down sequence are only recommended to minimize possible inrush current.

## LOGIC CONTROL TABLE

PE	Input Pulse				Output MOSFETs			
	INA	INB	INC	IND	SP1 to DP1	DN1 to SN1	SP2 to DP2	DN2 to SN2
1	1	X	X	X	ON	X	X	X
	X	1	X	X	X	ON	X	X
	X	X	1	X	X	X	ON	X
	X	X	X	1	X	X	X	ON
	0	X	X	X	OFF	X	X	X
	X	0	X	X	X	OFF	X	X
	X	X	0	X	X	X	OFF	X
	X	X	X	0	X	X	X	OFF
0	X	X	X	X	OFF	OFF	OFF	OFF

## 2.0 PAD DESCRIPTION

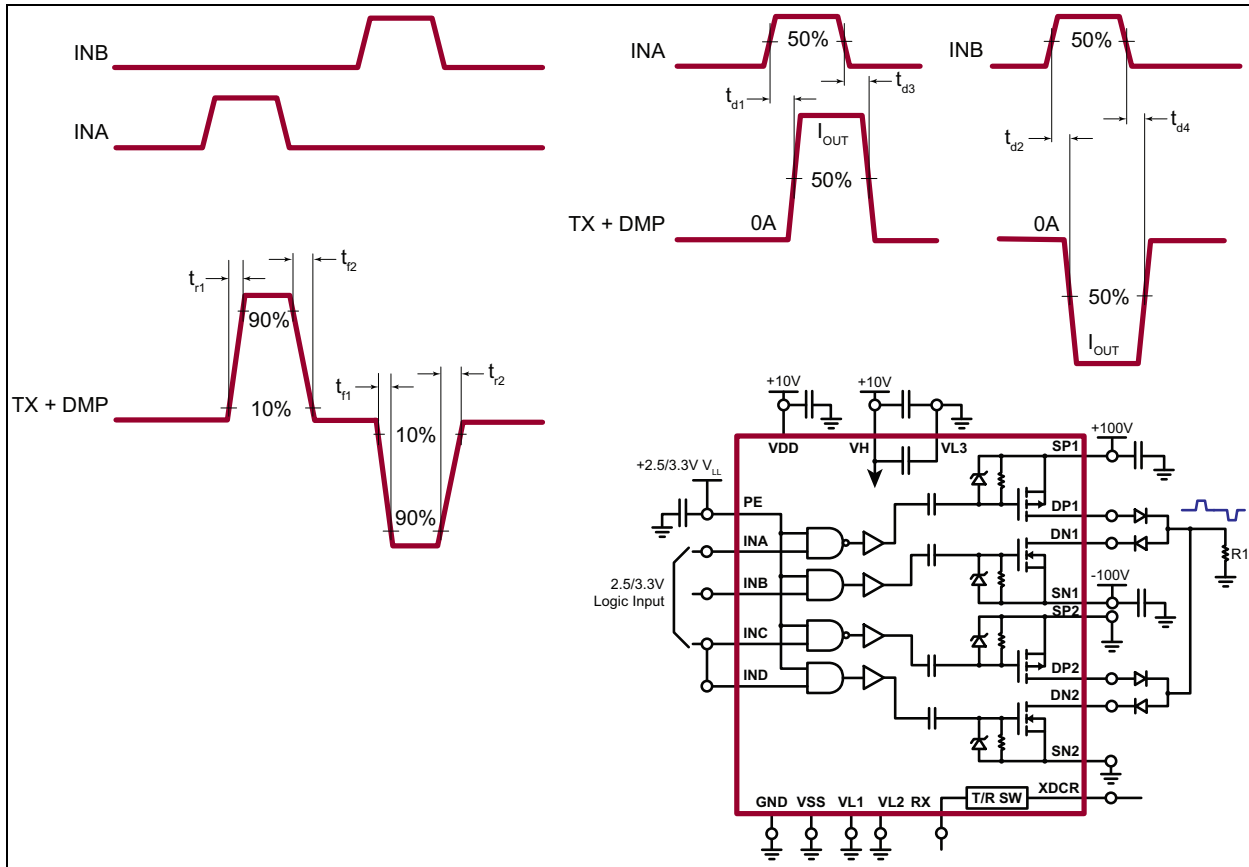
Table 2-1 details the description of pads in HV7360/HV7361.

**TABLE 2-1: PAD FUNCTION TABLE**

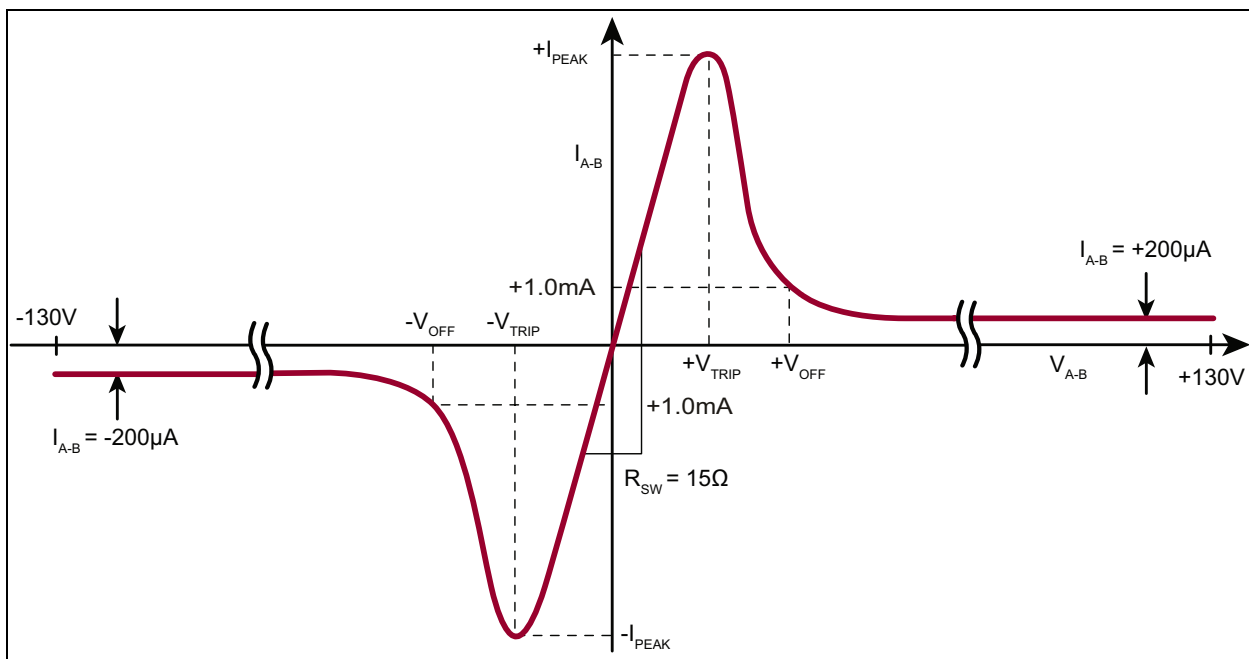
Pad Location	HV7360 Symbol	HV7361 Symbol	Description
A1	GND	GND	Driver and level translator circuit ground return (0V)
A2	IND	IND	Damping N-FET control signal logic input, controlling N-FET2
A3	INC	INC	Damping P-FET control signal logic input, controlling P-FET2
A4	V <sub>SS</sub>	V <sub>SS</sub>	Negative voltage power supply (0V)
A6	V <sub>DD</sub>	V <sub>DD</sub>	Positive voltage supply (+10V), should connect to an external decoupling cap to V <sub>SS</sub> (0V)
A7	INB	INB	Pulsing N-FET control signal logic input, controlling N-FET1
A8	INA	INA	Pulsing P-FET control signal logic input, controlling P-FET1
A9	PE	PE	Drive power enable Hi = On, Low = Off, logic '1' voltage reference input (+2.5V to +3.3V)
B2	V <sub>L2</sub>	V <sub>L2</sub>	Gate-drive negative voltage power supply (0V)
B8	V <sub>L1</sub>	V <sub>L1</sub>	Gate-drive negative voltage power supply (0V)
F4	V <sub>H</sub>	V <sub>H</sub>	Gate-drive positive voltage power supply (+10V)
F7	V <sub>L3</sub>	V <sub>L3</sub>	V <sub>H</sub> to V <sub>L</sub> decoupling cap. The trace connecting V <sub>L1</sub> , V <sub>L2</sub> , and V <sub>L3</sub> (0V) to ground plane should be as short as possible.
G4	NC	—	No connection for HV7360
	—	RX	T/R switch output for HV7361
P1	SP2	SP2	Source of P-FET2, positive high voltage power supply (0 to +100V) or GND
P2	DP2	DP2	Drain of P-FET2, transmit pulser output
P3	DN2	DN2	Drain of N-FET2, transmit pulser output
P4	SN2	SN2	Source of N-FET2, negative high voltage power supply (0 to -100V) or GND
P5	NC	—	No connection for HV7360
	—	XDCR	T/R switch input for HV7361
P6	SP1	SP1	Source of P-FET1, positive high voltage power supply (0 to +100V)
P7	DP1	DP1	Drain of P-FET1, transmit pulser output
P8	DN1	DN1	Drain of N-FET1, transmit pulser output
P9	SN1	SN1	Source of N-FET1, negative high voltage power supply (0 to -100V)

# HV7360/HV7361

## 3.0 FUNCTIONAL DESCRIPTION

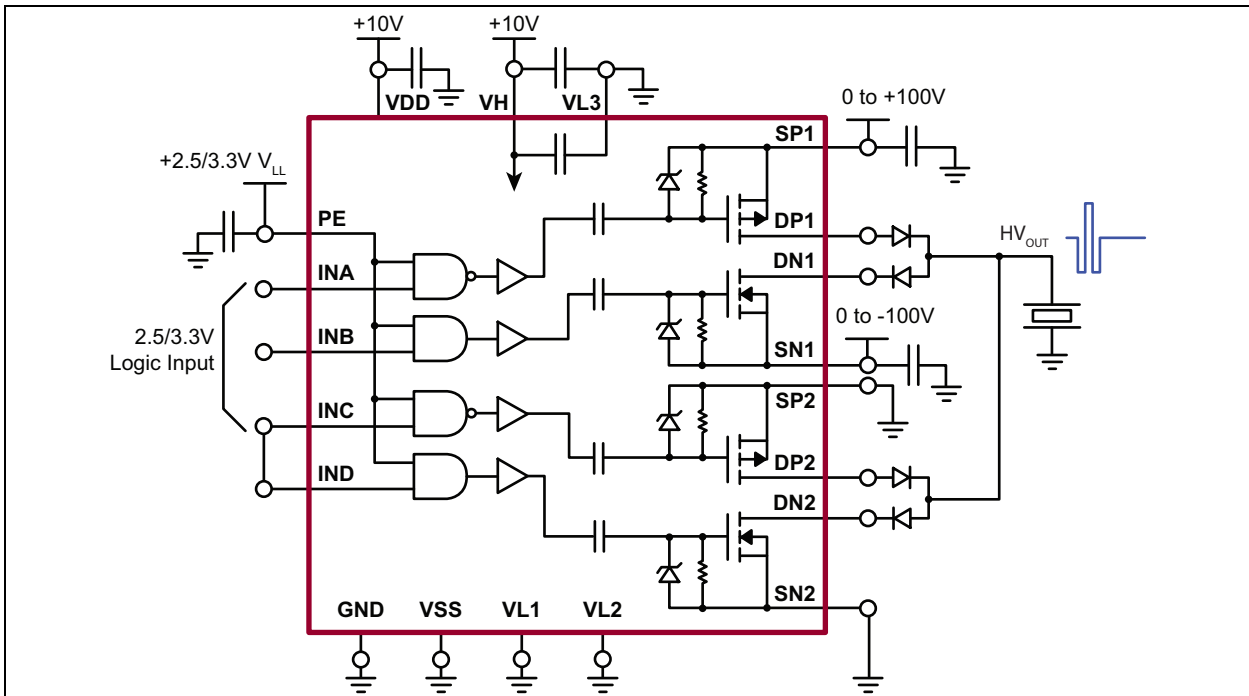


**FIGURE 3-1:** Pulser Timing Test for HV7360/HV7361.

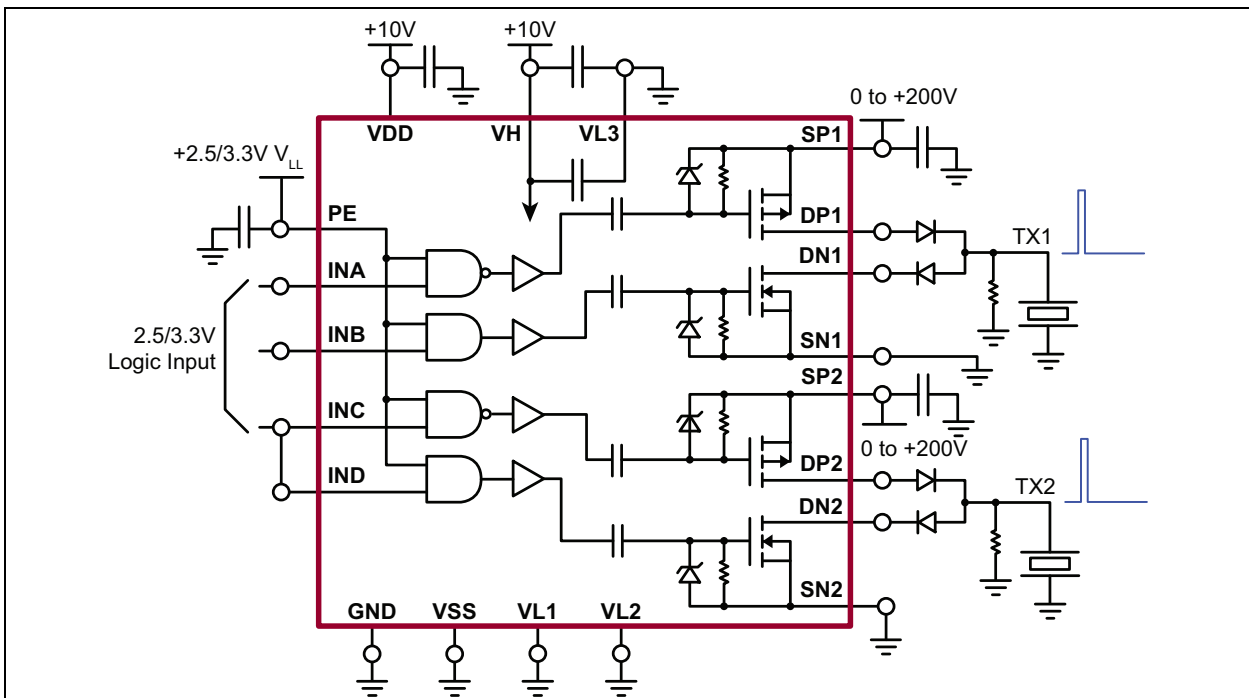


**FIGURE 3-2:** T/R Switch I-V curve for HV7361.





**FIGURE 3-3:** Typical Bipolar One-channel Three-level Ultrasound Transmitter Application Circuit for HV7360.



**FIGURE 3-4:** Typical Unipolar Two-channel Two-level Ultrasound Transmitter Application Circuit for HV7361.

# HV7360/HV7361

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## 4.0 PACKAGING INFORMATION

### 4.1 Package Marking Information

XXXXXX  
XX <sup>(e3)</sup>  
YYWWNNN

HV7360  
GA <sup>(e3)</sup>  
1624111

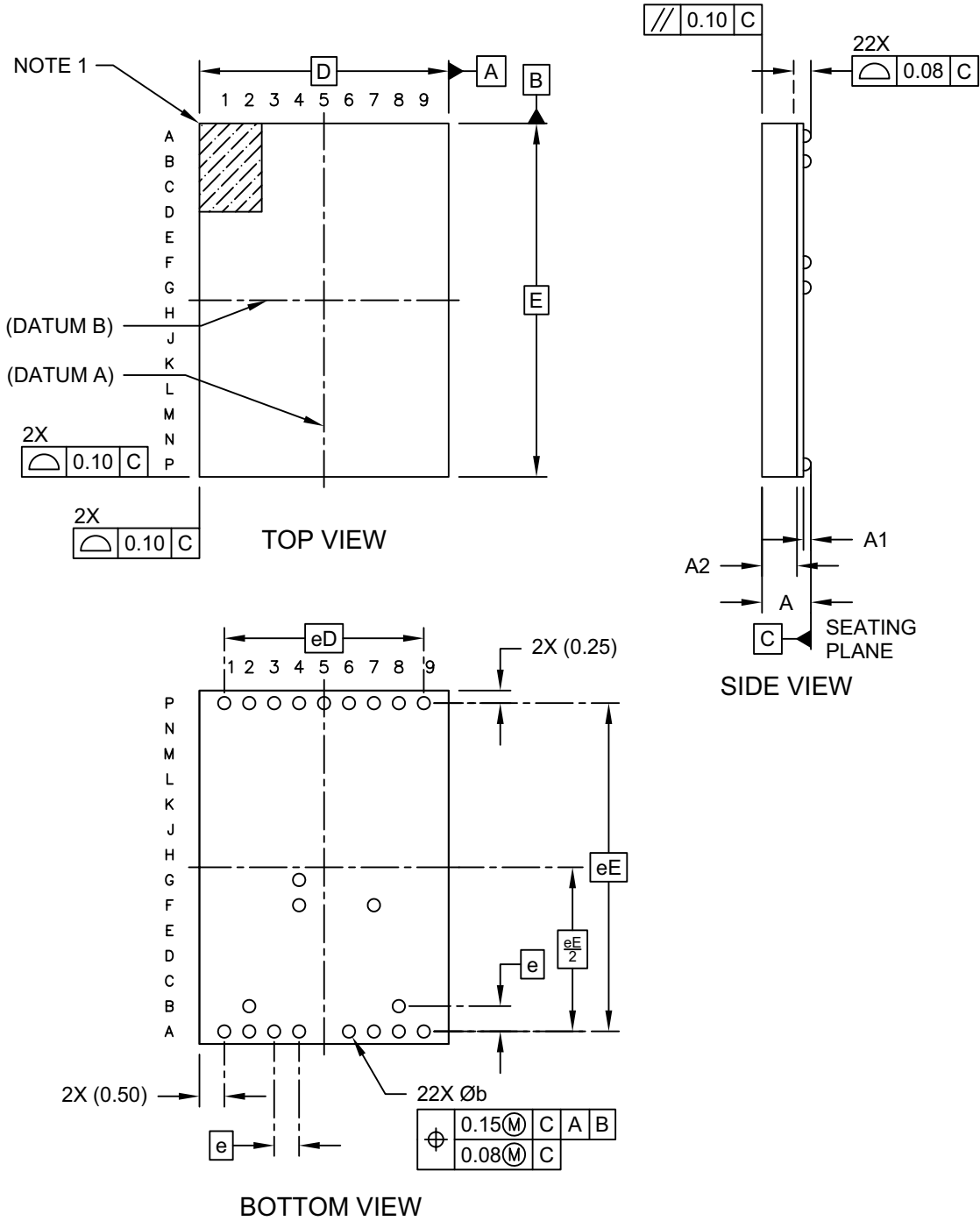
XXXXXX  
XX <sup>(e3)</sup>  
YYWWNNN

HV7361  
GA <sup>(e3)</sup>  
1618555

<b>Legend:</b>	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	<sup>(e3)</sup>	Pb-free JEDEC <sup>®</sup> designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator <sup>(e3)</sup> can be found on the outer packaging for this package.
<b>Note:</b>	In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.	

## 22-Ball Chip Array Ball Grid Array (JY) - 5x7 mm Body [CABGA]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>

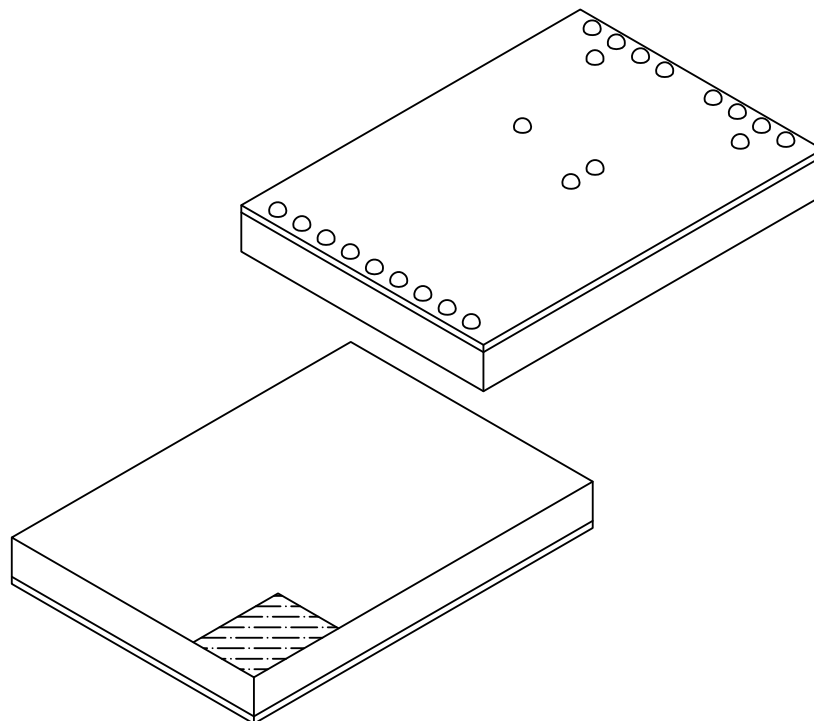


Microchip Technology Drawing C04-414A Sheet 1 of 2

# HV7360/HV7361

## 22-Ball Chip Array Ball Grid Array (JY) - 5x7 mm Body [CABGA]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Terminals	-	22		
Pitch	e	0.50 BSC		
Overall Height	A	0.91	0.98	1.05
Ball Height	A1	0.12	0.15	-
Package Thickness	A2	0.66	0.70	0.74
Overall Length	D	5.00 BSC		
Overall Terminal Pitch	eD	4.00 BSC		
Overall Width	E	7.00 BSC		
Overall Terminal Pitch	eE	6.50 BSC		
Ball Diameter	b	0.20	0.25	0.30

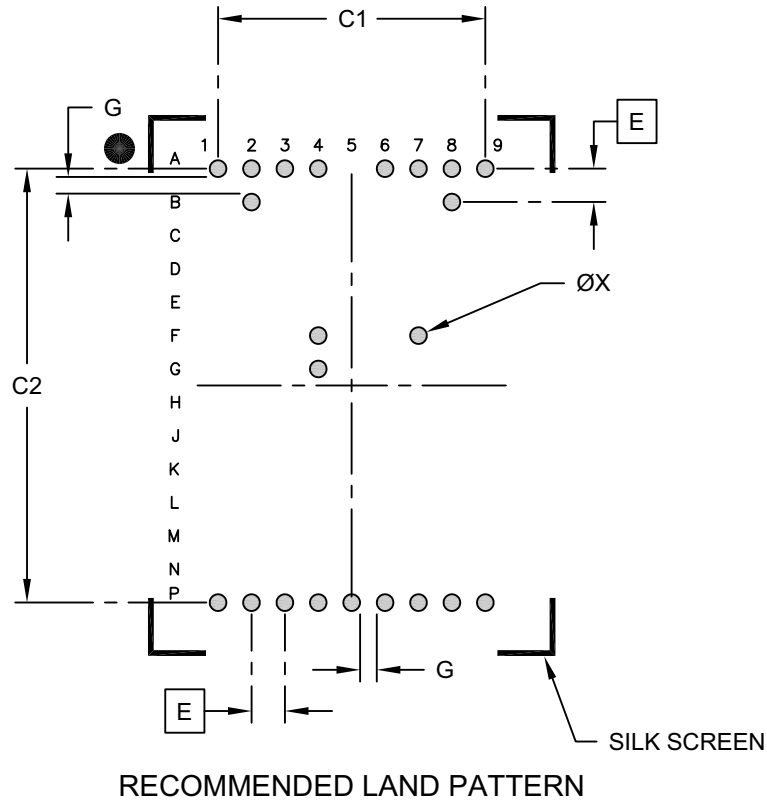
Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. Dimensioning and tolerancing per ASME Y14.5M  
BSC: Basic Dimension. Theoretically exact value shown without tolerances.  
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-414A Sheet 2 of 2

## 22-Ball Chip Array Ball Grid Array (JY) - 5x7 mm Body [CABGA]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.50 BSC		
Contact Pad Spacing	C1		4.00	
Contact Pad Spacing	C2		6.50	
Contact Pad Diameter (X22)	X		0.25	
Contact Pad to Contact Pad	G	0.20		

**Notes:**

- Dimensioning and tolerancing per ASME Y14.5M  
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2414A

# HV7360/HV7361

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NOTES:

# HV7360/HV7361

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## APPENDIX A: REVISION HISTORY

### Revision A (June 2016)

- Converted Supertex Doc# DSFP-HV7360 and Supertex Doc# DSFP-HV7361 to Microchip DS20005570A.
- Merged HV7360 and HV7361 into one document.
- Replaced the 22-lead LFGA “LA” package with 22-lead CABGA “GA” package.
- Made minor text changes throughout the document.

## PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

<u>PART NO.</u>					
Device	Package Options	-	Environmental	-	Media Type
Device:	HV7360	=	High-voltage High-speed Pulse Generator with Built-in Fast RTZ Damping FETs		
	HV7361	=	High-voltage High-speed Pulse Generator with Built-in Fast RTZ Damping FETs and an Integrated Two-terminal Low-noise T/R Switch		
Packages:	GA	=	22-lead CABGA		
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package		
Media Type:	(blank)	=	364/Tray for GA Package		

### Examples:

- a) HV7360GA-G: High-voltage High-speed Pulse Generator with Built-in Fast RTZ Damping FET, 22-lead CABGA Package, 364/Tray
- b) HV7361GA-G: High-voltage High-speed Pulse Generator with Built-in Fast RTZ Damping FET and an Integrated Two-terminal Low-noise T/R Switch, 22-lead CABGA Package, 364/Tray



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